

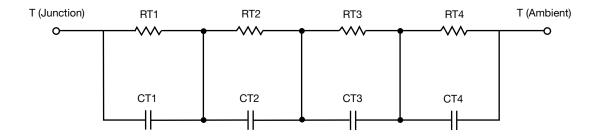
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	N/A	530.1450m	N/A		
RT2	N/A	314.1416m	N/A		
RT3	N/A	256.3613m	N/A		
RT4	N/A	494.9749m	N/A		
	THERMAL CAPAC	SITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	195.8836m	N/A		
CT2	N/A	54.8859m	N/A		
CT3	N/A	9.0504m	N/A		
CT4	N/A	1.8851m	N/A		

Note

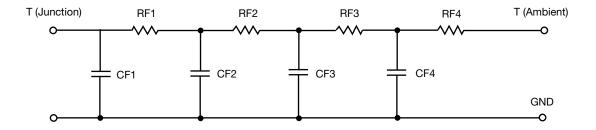
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	N/A	749.1903m	N/A			
RF2	N/A	390.8521m	N/A			
RF3	N/A	362.5694m	N/A			
RF4	N/A	93.2659m	N/A			
	THERMAL CAPAC	CITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	N/A	1.5208m	N/A			
CF2	N/A	28.5417m	N/A			
CF3	N/A	170.9369m	N/A			
CF4	N/A	1.2244m	N/A			

Note

• n/a indicates not applicable





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